

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	15m Ω @10V	30A
	20m Ω @4.5V	

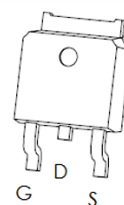
Feature

- Split Gate Trench Technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

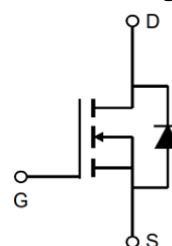
Application

- Power Management
- Motor Driving
- High frequency switching, synchronous rectification

TO252-2L



Schematic diagram



Package Marking and Ordering Information

Part Number	Package	Marking	Packing	Reel Size	Tape Width	Qty
GPT140N10LTF	TO-252-2L	T140N10L	Reel & Tape	330mm	16mm	2500pcs

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ¹	$T_C = 25^\circ\text{C}$	I_D	30	A
	$T_C = 100^\circ\text{C}$		19	
Pulsed Drain Current ²		I_{DM}	120	A
Single Pulsed Avalanche Current ³		I_{AS}	14	A
Single Pulsed Avalanche Energy ³		E_{AS}	49	mJ
Power Dissipation ⁵		P_D	50	W
$T_C = 25^\circ\text{C}$				
Thermal Resistance from Junction to Ambient ⁶		$R_{\theta JA}$	50	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case		$R_{\theta JC}$	2.5	$^\circ\text{C/W}$
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~ +150	$^\circ\text{C}$

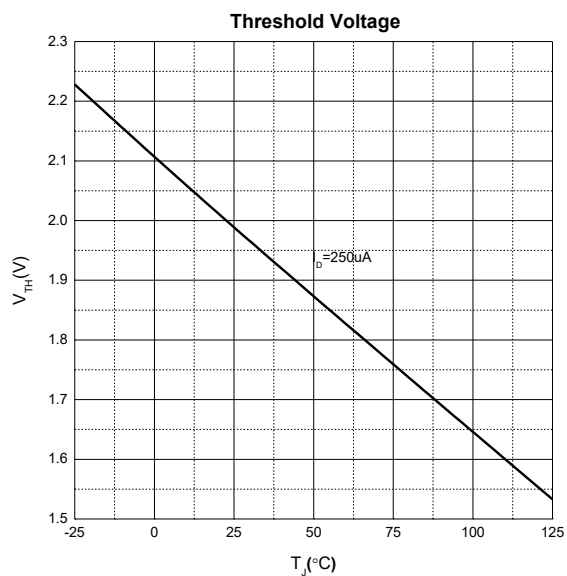
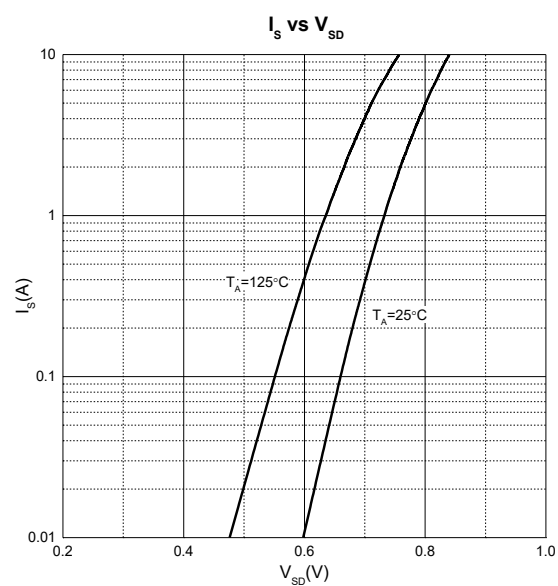
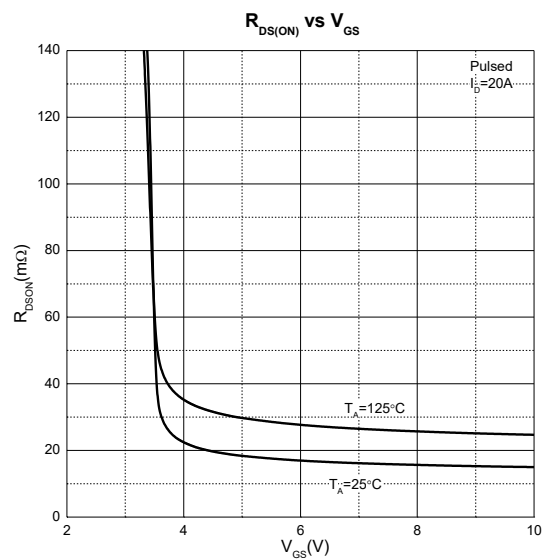
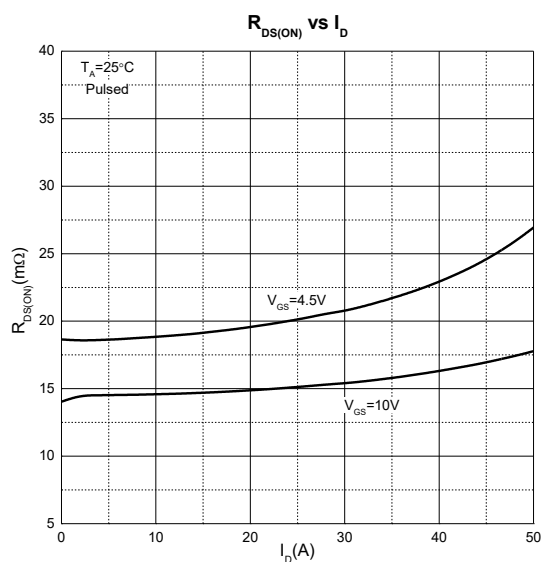
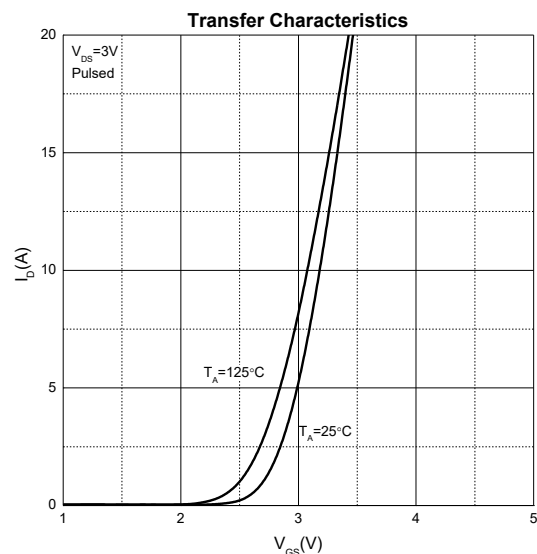
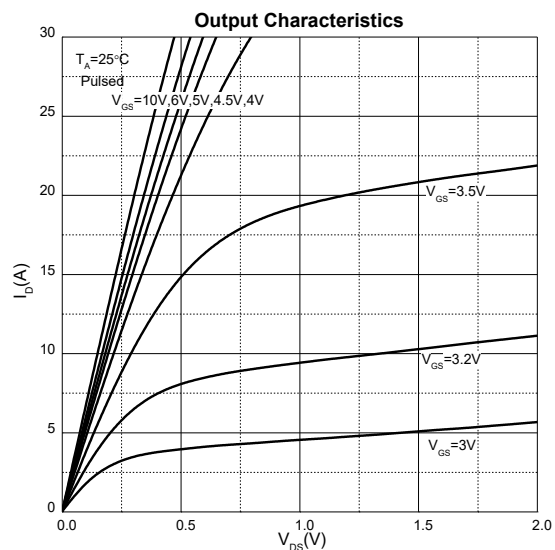
MOSFET ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

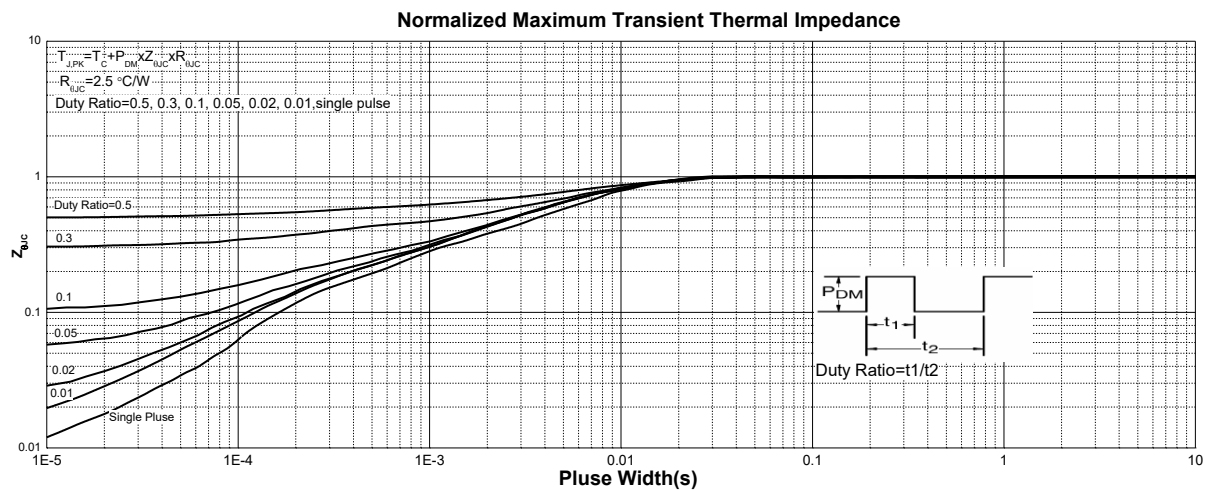
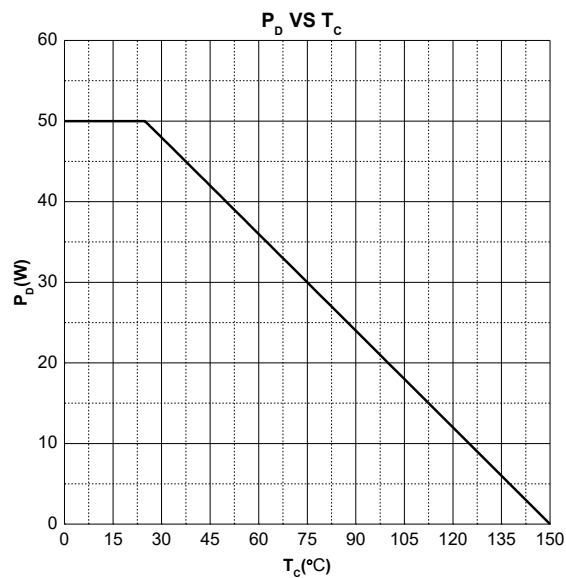
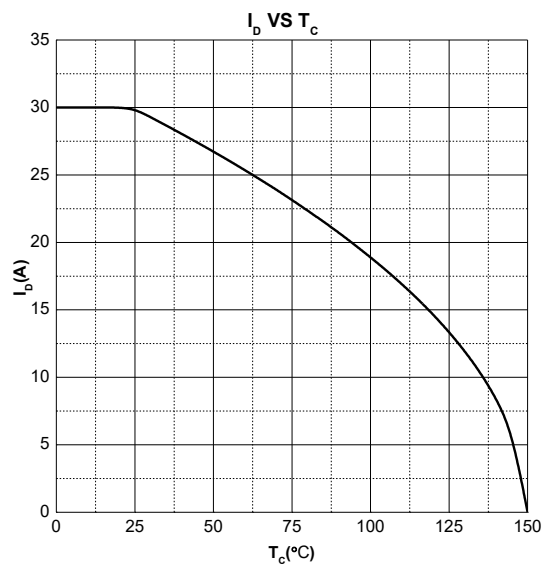
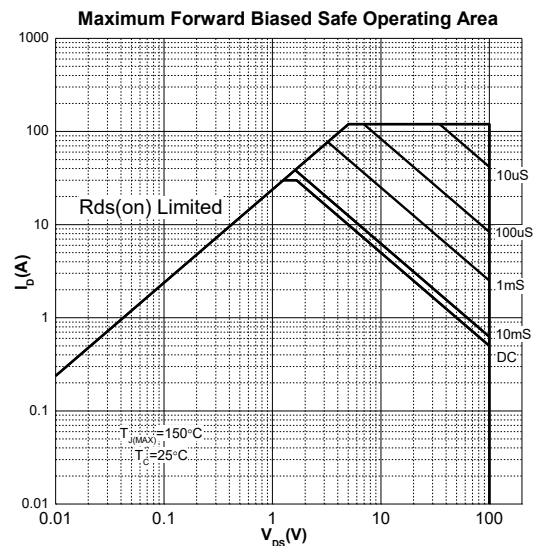
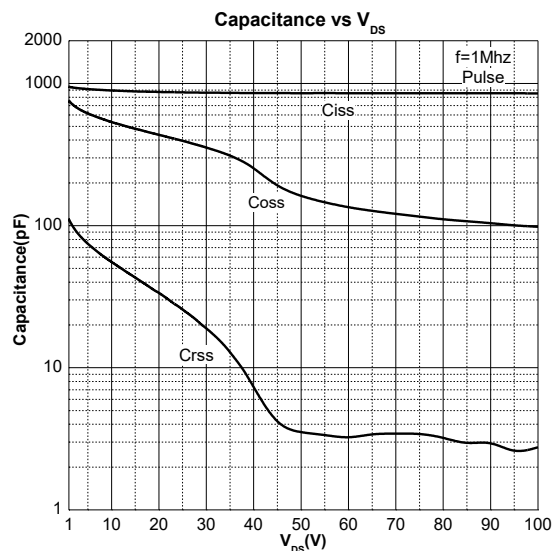
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100V, V _{GS} = 0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
On Characteristics ⁴						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.5	2.0	2.5	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 20A		15	20	mΩ
		V _{GS} = 4.5V, I _D = 10A		20	25	mΩ
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = 50V, V _{GS} = 0V, f = 1MHz		850		pF
Output Capacitance	C _{oss}			159		
Reverse Transfer Capacitance	C _{rss}			3.4		
Gate Resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		2.2		Ω
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} = 50V, V _{GS} = 10V, I _D = 20A		14		nC
Gate-Source Charge	Q _{gs}			3.0		
Gate-Drain Charge	Q _{gd}			2.5		
Gate Plateau Voltage	V _{plateau}			3.4		V
Turn-On Delay Time	t _{d(on)}	V _{DD} = 50V, V _{GS} = 10V, R _G = 3Ω, RL = 2.5Ω		4.5		ns
Turn-On Rise Time	t _r			3.8		
Turn-Off Delay Time	t _{d(off)}			15		
Turn-Off Fall Time	t _f			6.0		
Source-Drain Diode Characteristics						
Diode Forward Voltage ⁴	V _{SD}	V _{GS} = 0V, I _S = 20A			1.2	V
Diode Continuous Forward Current ¹	I _S	T _C = 25℃			30	A
Diode Pulse Forward Current ²	I _{SM}	T _C = 25℃			120	A
Diode Reverse Recovery Time	t _{rr}	I _F = 20A, dI/dt = 100A/μs		40		ns
Diode Reverse Recovery Charge	Q _{rr}	I _F = 20A, dI/dt = 100A/μs		50		nC

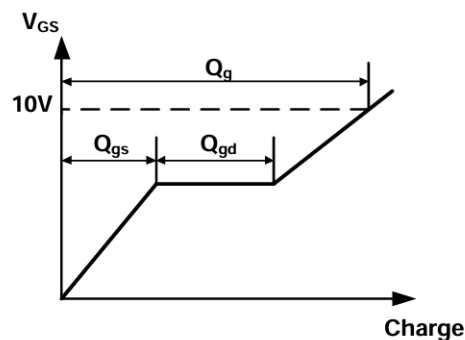
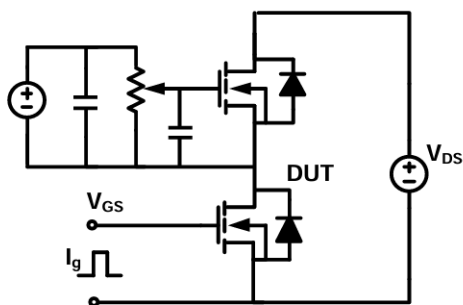
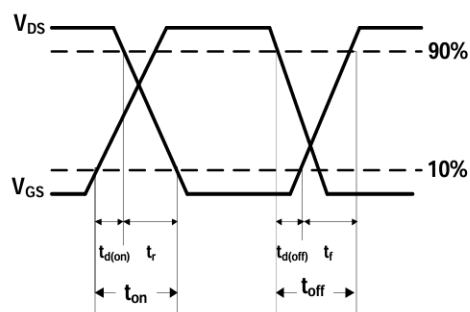
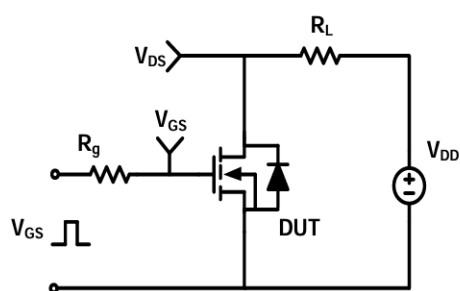
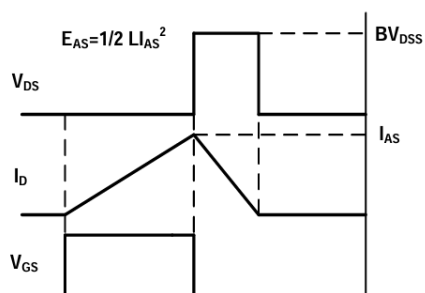
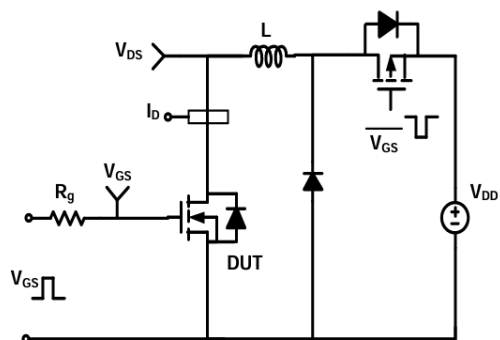
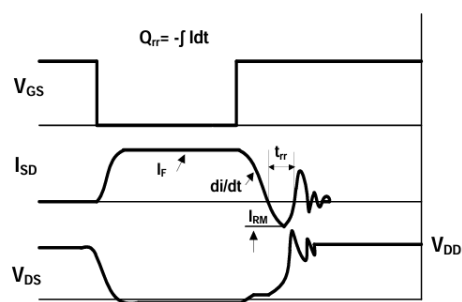
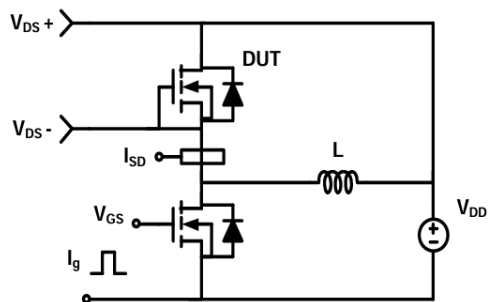
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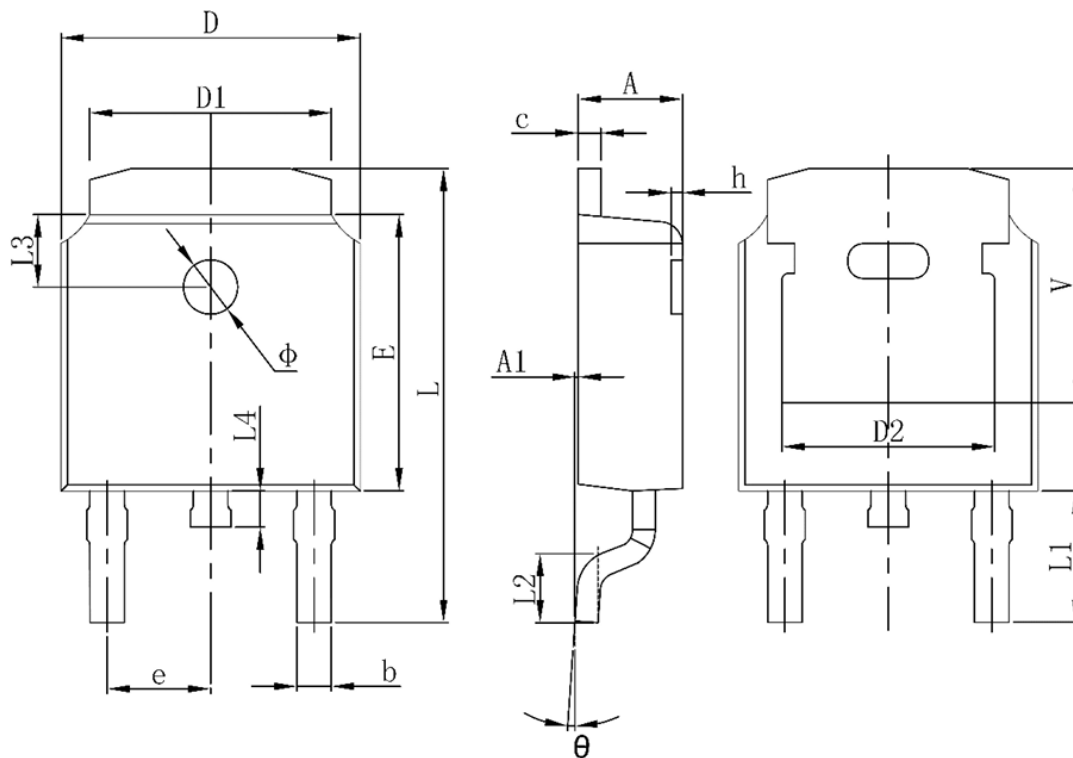
- 1.The maximum current rating is limited by package. And device mounted on a large heatsink.
- 2.Pulse Test: Pulse Width ≤ 10μs, duty cycle ≤ 1%.
- 3.EAS condition: V_{DD} = 50V, V_{GS} = 10V, L = 0.5mH, R_G = 25Ω Starting T_J = 25°C.
- 4.Pulse Test: Pulse Width ≤ 300μs, duty cycle ≤ 2%.
- 5.The power dissipation P_D is limited by T_{J(MAX)} = 150°C. And device mounted on a large heatsink.
- 6.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C.

Typical Characteristics





Test Circuit
Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveform

Unclamped Inductive Switching (UIS) Test Circuit & Waveform

Diode Recovery Test Circuit & Waveform


TO252-2L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.130	0.000	0.005
b	0.590	0.860	0.023	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830REF		0.190REF	
E	6.000	6.300	0.236	0.248
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900REF		0.114REF	
L2	1.400	1.700	0.055	0.067
L3	1.600REF		0.063REF	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250REF		0.207REF	

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.